

## Phototransistor chip FT232

### Description

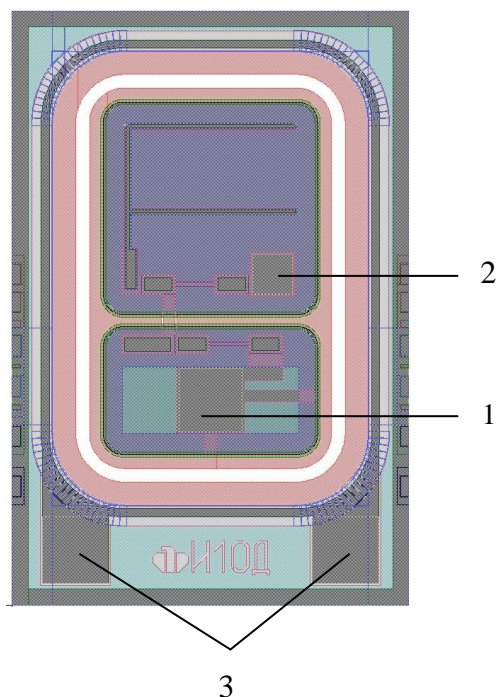
FT232 chip is fabricated using Silicon Bipolar process technology with high-ohmic polysilicon shunt. It is designed to be used in optocouplers. The maximum spectral response range is 0.85-0.92 nm.

### Features

- Photosensitive Area - 0.7x0.7 mm
- Chip Size - 1x1.5 mm
- Chip Thickness - 0.35±0.02 mm
- High-ohmic Shunt
- Contact pads material – Aluminum
- Metallization: bottom – Si

### Absolute Maximum Ratings

Storage Temperature	-65°C to 150°C
Operating Junction Temperature	-60°C to 125°C



- 1 - Emitter  
2 - Base  
3 - Collector

### Electrical Parameters (T= 25°C)

Parameter	Symbol	Unit	Min.	Typ.	Max.	Conditions
Collector-Emitter Dark current	$I_{CE0}$	$\mu A$		0.05	0.1	$V_{CE} = 220 V$
Breakdown Voltage Collector-Emitter	$BV_{CEOL}$	V	160	180		$I_C = 10 mA$
Collector-Emitter Saturation Voltage	$V_{CE SAT}$	V	-	0.9	1.2	$I_B = 50 \mu A, I_C = 5 mA$
Current Transfer Ratio	$h_{21E}$		400		2500	$I_B = 50 \mu A, V_{CE} = 5 V$
Polysilicon Shunt Resistance	R	MOhm	0.0625	0.12	0.25	$V_{EB} = 5 V$